## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re I	Patent Application of	)	
Shun	oei YAMAZAKI et al.	)	ATTN: New Applications
Based	d On: JP 2002-276379	)	
Filed:	September 20, 2002	)	
For:	MANUFACTURING METHOD	)	
	OF SEMICONDUCTOR DEVICE	= )	

## **INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

In accordance with the provisions of 37 C.F.R. 1.56 and 37 C.F.R. 1.97-1.99, Applicant submits herewith a Form PTO-1449 listing references known to Applicant and requests that these references be made of record in the above identified application. Copies of the references listed are submitted herewith in accordance with 37 C.F.R. 1.98(a).

- U.S. Patent No. 6,475,912 is in the family of Japanese Patent Laid-Open No. 2000-58650.
- U.S. Patent Publication 2001/0015618 is in the family of Japanese Patent Laid-Open No. 2001-236025.
- U.S. Patent Publication 2001/0030322 is in the family of Japanese Patent Laid-Open No. 2001-313397.
- U.S. Patent No. 6,413,845 is in the family of Japanese Patent Laid-Open No. 2000-357671.

The Examiner's attention is also directed to related U.S. Patent Application Serial No. 10/245,701.

The Commissioner is hereby authorized to charge fees under 37 C.F.R. §§1.16, 1.17, 1.20(a), 1.20(b), 1.20(c), and 1.20(d) (except the Issue Fee) which may be

required now or hereafter, or credit any overpayment to Deposit Account No. 50-2280. A duplicate copy of this sheet is attached.

Respectfully submitted,

Eric J. Robinson

Reg. No. 38,285

Robinson Intellectual Property Law Office, P.C.

PMB 955

21010 Southbank Street

Potomac Falls, Virginia 20165

(571) 434-6789

Approved for use through 10/31/2002. OMB 0651-0031 U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

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Substitute	for form 1449A/PTO			Complete if Known		
INFO	RMATION I	DISCI	LOSURE	Application Number		
STATEMENT BY APPLICANT				Filing Date	September 10, 2003	
SIAI	(use as many sheets as necessary)			First Named Inventor	Shunpei YAMAZAKI et al.	
				Group Art Unit		
				Examiner Name		
Sheet	2	of	2	Attorney Docket Number	0756-7196	

				U.S. PATENT DOCUMENT	ΓS	
Examiner Initials	Cite No. 1	U.S. Patent Document		Name of Patentee or Applicant of Cited	Date of Publication of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)	Applicant of Cited Document	MM-DD-YYYY	Figures Appear	T <sub>e</sub>	
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			0	THER PRIOR	ART – NON PATENT LITE	RATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.)., date, page(s), volume-issue number(s), publisher, city and/or country where published.							
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ļ	Examiner	Date	
	Signature	Consider	ed

<sup>\*</sup>EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Substitute	e for form 1449A/PTO			, Co	omplete if Known
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SIAI	STATEMENT BY APPLICANT		First Named Inventor	Shunpei YAMAZAKI et al.	
	(use as many sheets o	as necesso	iry)	Group Art Unit	
				Examiner Name	
Sheet	1	of	2	Attorney Docket Number	0756-7196

		-	U.S. PATENT DOCUMEN	TS	
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Examiner	Date	
Signature	Considered	

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